

Please amend the subject application as follows:

IN THE CLAIMS:

Please accept amended claims 1, 23 and 25 and new claim 32 as follows:

1. (currently amended) A capacitor comprising:
a lower electrode formed on a semiconductor substrate;
a dielectric film stacked on the lower electrode; and
an upper electrode, comprising a first upper electrode and a second upper electrode, formed on the dielectric film, wherein:

the first upper electrode is formed by physical vapor deposition without bias power applied to the semiconductor substrate and the second upper electrode is formed by chemical vapor deposition,

an interlayer dielectric is formed on the capacitor,

a portion of the interlayer dielectric is overetched to expose the second upper electrode, and

a thickness of the first and second upper electrodes prevents overetching of the upper electrode.

2. (original) The capacitor of claim 1, wherein the upper electrode is made of one selected from the group consisting of titanium nitride, tantalum nitride, tungsten nitride, ruthenium, platinum, iridium, and a combination thereof.

3. (canceled)

4. (previously presented) The capacitor of claim 1, wherein the first upper electrode and the second upper electrode are sequentially stacked.

5. - 22. (canceled)

23. (currently amended) A capacitor comprising:

a lower electrode formed on a semiconductor substrate;

a dielectric film stacked on the lower electrode; and

an upper electrode formed on the dielectric film, wherein:

the upper electrode is formed by physical vapor deposition and one of chemical vapor deposition and atomic layer deposition, [[and]]

the upper electrode includes a first upper electrode formed by the physical vapor deposition without bias power applied to the semiconductor substrate and a second upper electrode formed by one of the chemical vapor deposition and the atomic layer deposition,

an interlayer dielectric is formed on the capacitor,

a portion of the interlayer dielectric is overetched to expose the second upper electrode, and

a thickness of the first and second upper electrodes prevents overetching of the upper electrode.

24. (canceled)

25. (currently amended) A capacitor comprising:
a lower electrode formed in a concave hole and on a semiconductor substrate;
a dielectric film stacked on the lower electrode; and
an upper electrode formed on the dielectric film, wherein:
the upper electrode includes a first upper electrode formed by physical vapor deposition without bias power applied to the semiconductor substrate to form the first upper electrode on a sidewall of the concave hole,
an interlayer dielectric is formed on the capacitor,
a portion of the interlayer dielectric is overetched to expose the second upper electrode, and
a thickness of the first and second upper electrodes prevents overetching of the upper electrode.
26. (canceled)
27. (previously presented) The capacitor of claim 25, wherein the upper electrode further includes a second upper electrode formed by chemical vapor deposition.
28. (previously presented) The capacitor of claim 1, wherein the capacitor is a concave-type capacitor.

29. (previously presented) The capacitor of claim 23, wherein the capacitor is a concave-type capacitor.

30. (previously presented) The capacitor of claim 25, wherein the capacitor is a concave-type capacitor.

31. (previously presented) The capacitor of claim 27, further comprising an anti-reflective layer formed on the second upper electrode.

32. (new) The capacitor of claim 31, wherein a thickness of the anti-reflective layer is in a range of about 400 angstroms to about 500 angstroms.